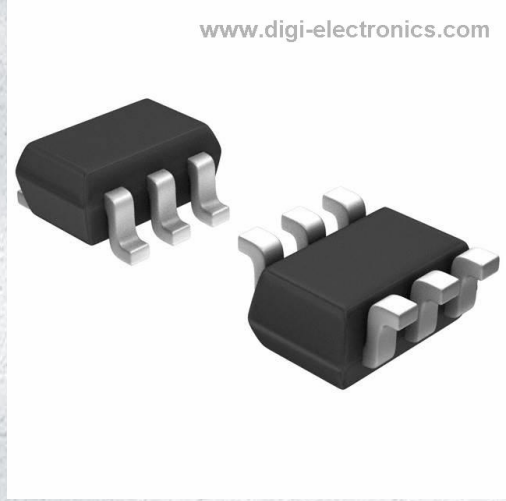
NVJS3151PT1G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	NVJS3151PT1G-DG
Manufacturer	onsemi
Manufacturer Product Number	NVJS3151PT1G
Description	MOSFET P-CH 12V 2.7A SC88
Detailed Description	P-Channel 12 V 2.7A (Ta) 625mW (Ta) Surface Mount SC-88/SC70-6/SOT-363

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NVJS3151PT1G	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
12 V	2.7A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	60mOhm @ 3.3A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.2V @ 100µA	8.6 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	850 pF @ 12 V
FET Feature:	Power Dissipation (Max):
-	625mW (Ta)
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
SC-88/SC70-6/SOT-363	6-TSSOP, SC-88, SOT-363
Base Product Number:	
NVJS31	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

NTJS3151P, NVJS3151P

MOSFET – Power, Single, P-Channel, Trench, ESD Protected, SC-88

12 V, 3.3 A

Features

- Leading Trench Technology for Low $R_{DS(ON)}$ Extending Battery Life
- SC−88 Small Outline (2x2 mm, SC70−6 Equivalent)
- Gate Diodes for ESD Protection
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain−to−Source Voltage			V_{DSS}	−12	V
Gate−to−Source Voltage			V_{GS}	±12	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25 °C	I_D	−2.7	A
		T_A = 85 °C		−2.0	
	t ≤ 5 s	T_A = 25 °C		−3.3	
Power Dissipation (Note 1)	Steady State	T_A = 25 °C	P_D	0.625	W
Pulsed Drain Current		t_p = 10 μs	I_{DM}	−8.0	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−0.8	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Units
Junction−to−Ambient − Steady State	$R_{\theta JA}$	200	°C/W
Junction−to−Ambient − t ≤ 5 s	$R_{\theta JA}$	141	
Junction−to−Lead − Steady State	$R_{\theta JL}$	102	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

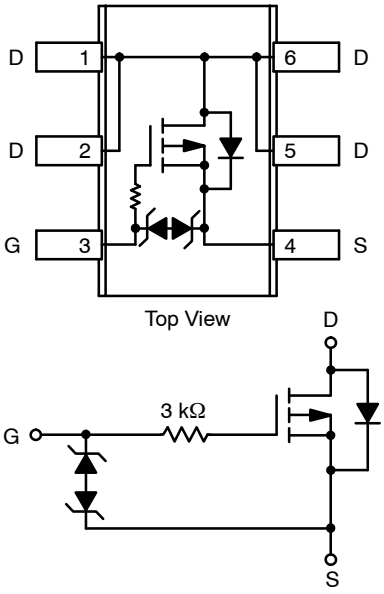
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ON Semiconductor®

www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
−12 V	45 mΩ @ −4.5 V	−3.3 A
	67 mΩ @ −2.5 V	
	133 mΩ @ −1.8 V	

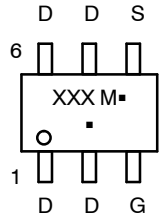
SC−88 (SOT−363)



MARKING DIAGRAM & PIN ASSIGNMENT

1

SC−88/SOT−363
CASE 419B
STYLE 28



XXX = Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NTJS3151P, NVJS3151P

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−12			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				10		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = −9.6 V, V_{DS} = 0 V	T_J = 25°C			−1.0	μA
			T_J = 125°C		−2.5		
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±4.5 V				±1.5	μA
		V_{DS} = 0 V, V_{GS} = ±12 V				±10	mA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 100 μA		−0.40		−1.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				3.4		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −3.3 A			45	60	mΩ
		V_{GS} = −2.5 V, I_D = −2.9 A			67	90	
		V_{GS} = −1.8 V, I_D = −1.0 A			133	160	
Forward Transconductance	g_{FS}	V_{GS} = −10 V, I_D = −3.3 A			15		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −12 V			850		pF
Output Capacitance	C_{OSS}				170		
Reverse Transfer Capacitance	C_{RSS}				110		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −5.0 V, I_D = −3.3 A			8.6		nC
Gate−to−Source Charge	Q_{GS}				1.3		
Gate−to−Drain Charge	Q_{GD}				2.2		
Gate Resistance	R_G				3000		Ω
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −6.0 V, I_D = −1.0 A, R_G = 6.0 Ω			0.86		μs
Rise Time	t_r				1.5		
Turn−Off Delay Time	$t_{d(OFF)}$				3.5		
Fall Time	t_f				3.9		
DRAIN−SOURCE DIODE CHARACTERISTICS (Note 2)							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −3.3 A	T_J = 25°C		−0.85	−1.2	V
			T_J = 125°C		−0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

NTJS3151P, NVJS3151P

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

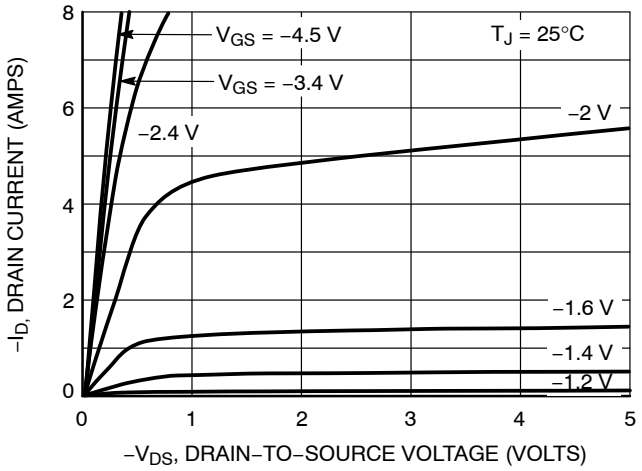


Figure 1. On−Region Characteristics

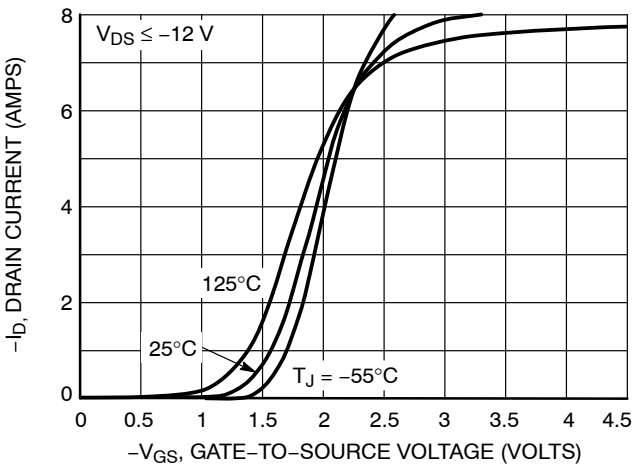


Figure 2. Transfer Characteristics

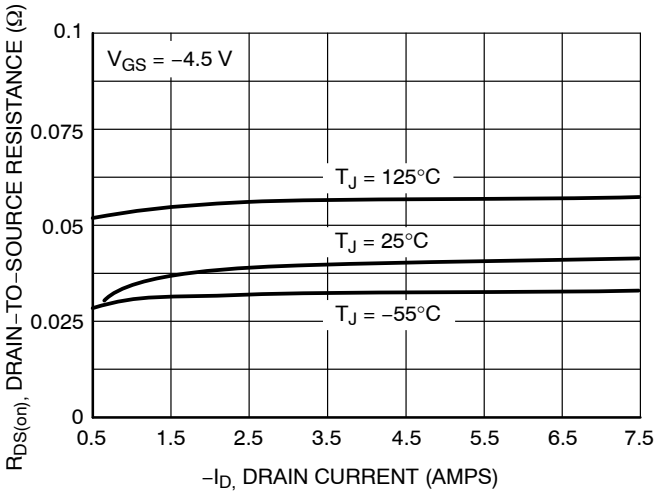


Figure 3. On−Resistance vs. Drain Current and Temperature

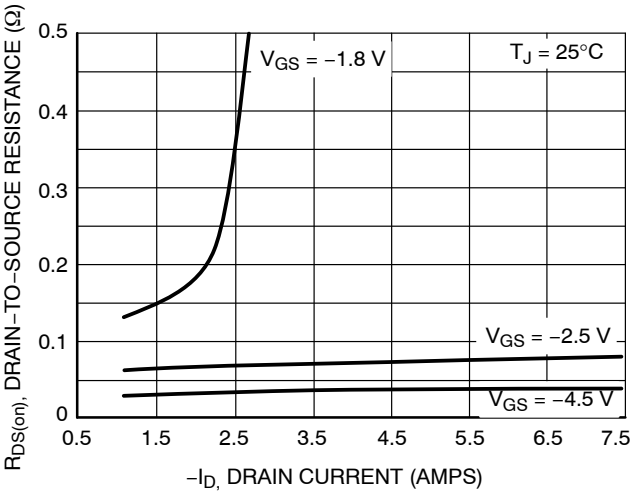


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

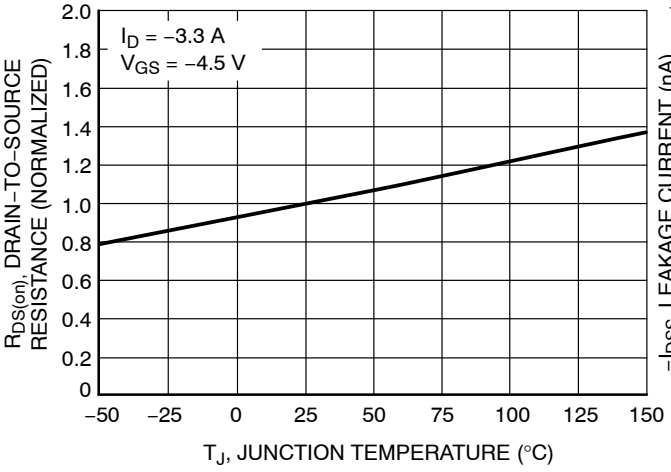


Figure 5. On−Resistance Variation with Temperature

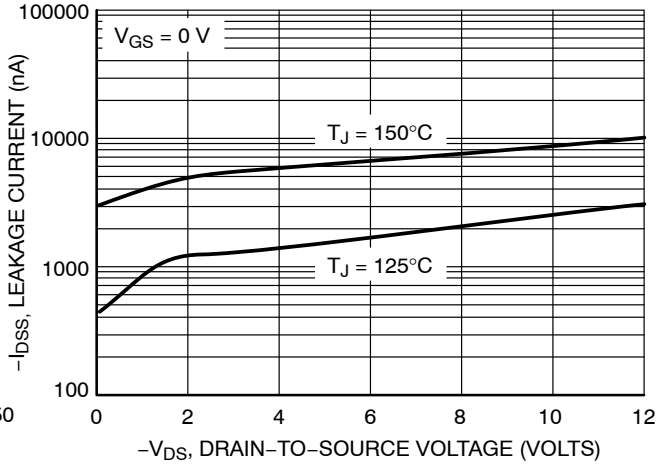


Figure 6. Drain−to−Source Leakage Current vs. Voltage

NTJS3151P, NVJS3151P

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

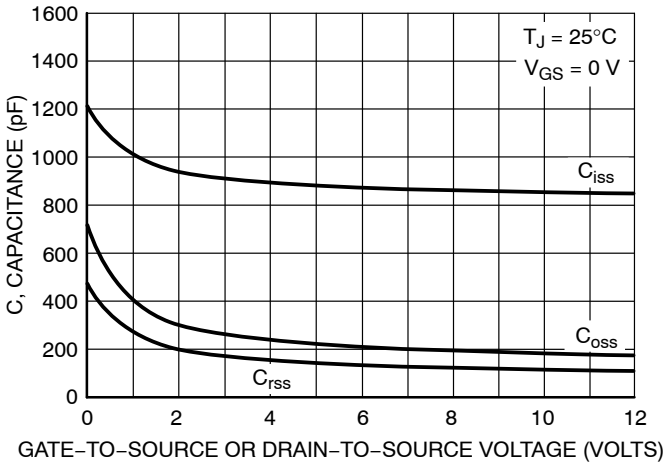


Figure 7. Capacitance Variation

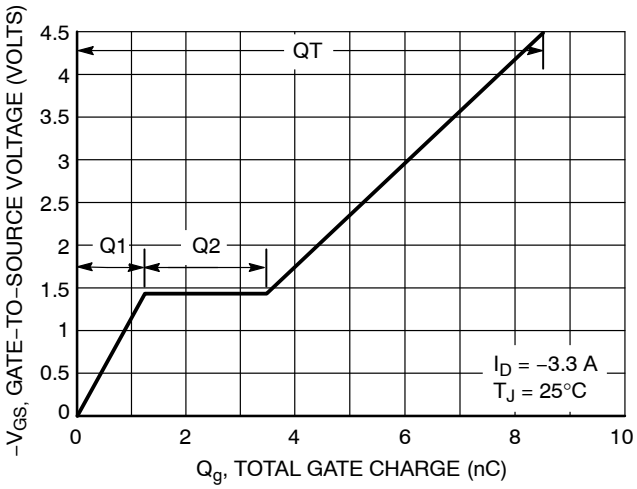


Figure 8. Gate−to−Source Voltage vs. Total Gate Charge

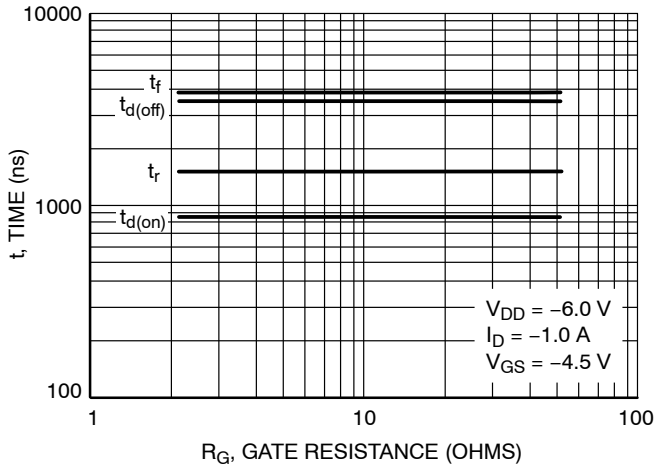


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

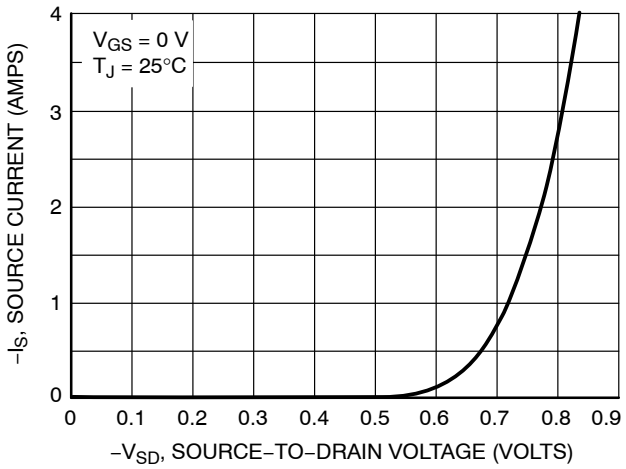


Figure 10. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Marking	Package	Shipping†
NTJS3151PT1G	TJ	SC−88 (Pb−Free)	3000 / Tape & Reel
NTJS3151PT2G	TJ		
NVJS3151PT1G*	VTJ		

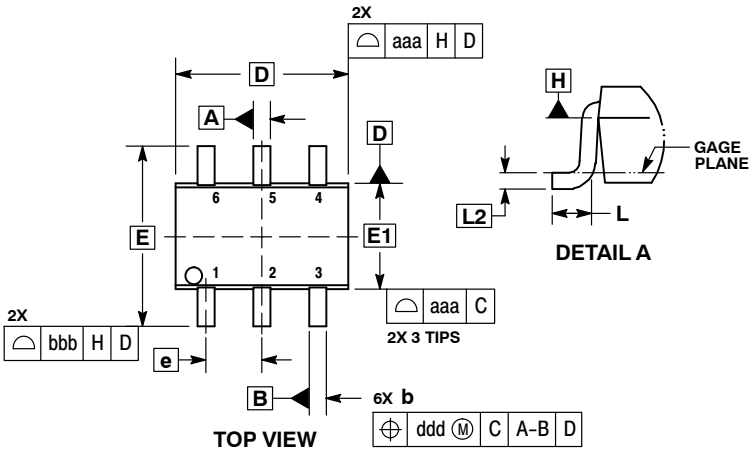
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

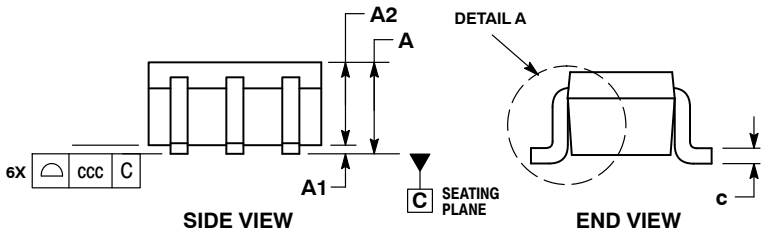
*NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

NTJS3151P, NVJS3151P

PACKAGE DIMENSIONS

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y



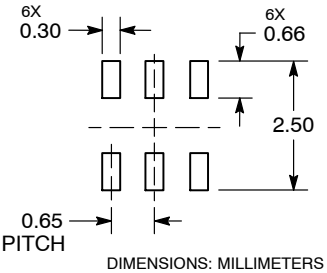


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

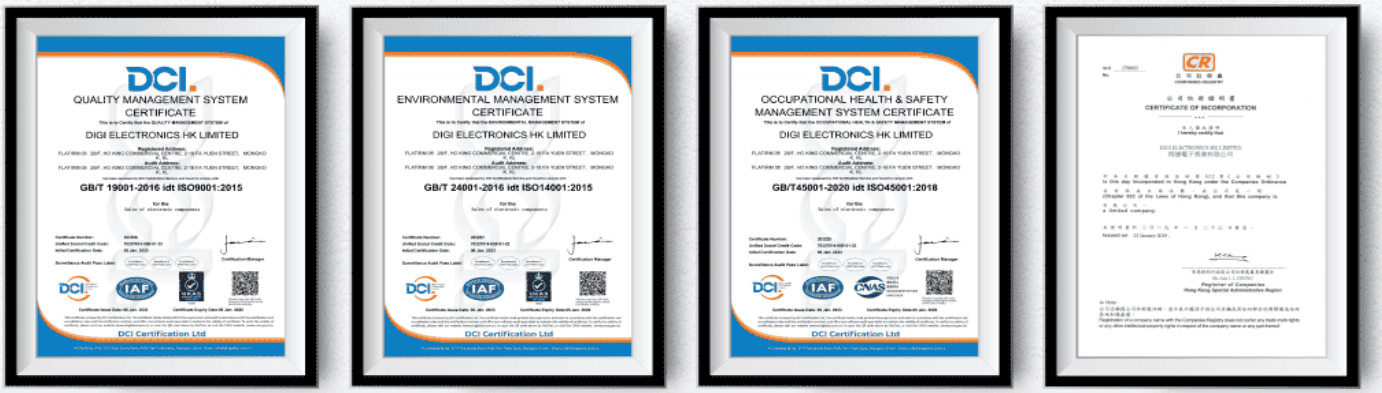
ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



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